New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A. TELEPHONE: (973) 376-2922

(212) 227-6005

FAX: (973) 376-8960

Picoampere diode

BAV45

FEATURES

- Extremely low leakage current: max. 5 pA
- · Low diode capacitance
- · Light insensitive.

APPLICATION

- Clamping
- Holding
- · Peak follower
- · Time delay circuits
- · Logarithmic amplifiers
- Protection of insulated gate field-effect transistors.

DESCRIPTION

Silicon diode in a metal TO-18 can. It has an extremely low leakage current over a wide temperature range combined with a low capacitance and is not sensitive to light.

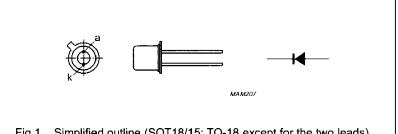


Fig.1 Simplified outline (SOT18/15; TO-18 except for the two leads) and symbol.

CAUTION

Handle the device with care whilst soldering into the circuit. The extremely low leakage current can only be guaranteed when the bottom is free from solder flux or other contaminations.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		-	35	V
V _R	continuous reverse voltage		_	20	V
l _F	continuous forward current	see Fig.2		50	mA
I _{FRM}	repetitive peak forward current		-	100	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+125	°C
T _i	junction temperature		_	125	°C

Note

1. Device mounted on a FR4 printed-circuit board.



Picoampere diode

BAV45

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	I _F = 10 mA; see Figs 3 and 4	1	V
I _R	reverse current	see Fig.5		
		V _R = 5 V	5	pА
		$V_R = 5 \text{ V}; T_j = 80 ^{\circ}\text{C}$	250	pΑ
		V _R = 20 V	10	pΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	1.3	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	600	ns

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient; note 1		K/W

Note

1. Device mounted on a FR4 printed-circuit board.

Picoampere diode

BAV45

PACKAGE OUTLINE

